CMKD6263DO

ULTRAmini™
DUAL OPPOSING
HIGH VOLTAGE
SCHOTTKY DIODES

ULTRAmini™

SOT-363 CASE

Central™
Semiconductor Corp.

FEATURES:

- DUAL OPPOSING (DO) SCHOTTKY DIODES
- HIGH VOLTAGE (70V)
- LOW FORWARD VOLTAGE
- GALVANICALLY ISOLATED

DESCRIPTION:

The Central Semiconductor CMKD6263DO incorporates two galvanically isolated, High Voltage, low V_F Silicon Diodes with an opposing Anode/Cathode configuration, in a space saving SOT-363 surface mount package. These diodes are designed for fast switching applications requiring a low forward voltage drop. Marking code is **63D**.

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	70	V
Continuous Forward Current	I_F	15	mA
Forward Surge Current, tp=1.0 s	I_{FSM}	50	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	V_R=50V		98	200	nA
BV_R	I_R=10μA	70			V
V_F	I_F=1.0mA		395	410	mV
C_T	V_R=0V, f=1.0MHz			2.0	pF
t_{rr}	I_R=I_F=10mA, I_{rr}=1.0mA, R_L=100Ω			5.0	ns

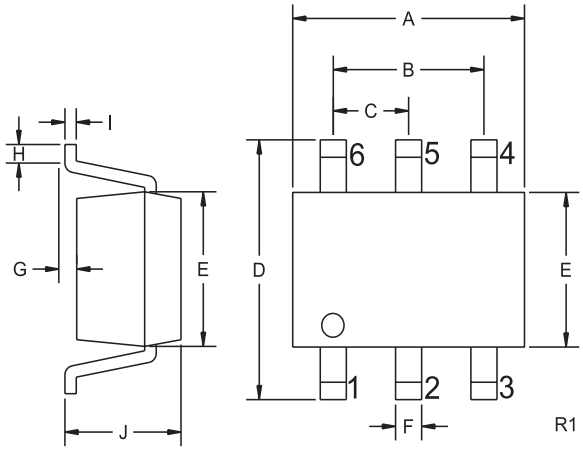
R0 (23-October 2001)

Central™
Semiconductor Corp.

CMKD6263DO

ULTRAmini™
DUAL OPPOSING
HIGH VOLTAGE
SCHOTTKY DIODES

SOT-363 CASE - MECHANICAL OUTLINE

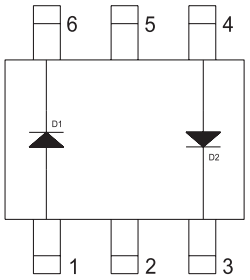


DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

MARKING CODE: 63D

Dual Opposing Configuration



LEAD CODE:

1) Anode D1
2) NC
3) Cathode D2
4) Anode D2
5) NC
6) Cathode D1

R0 (23-October 2001)